




<b>PCN Number:</b>	20170616002A		<b>PCN Date:</b>	Jul 17, 2017																			
<b>Title:</b>	Qualification of MIHO8 as an additional wafer fab site option for select devices in LBC7 process technology																						
<b>Customer Contact:</b>	PCN Manager		<b>Dept:</b>	Quality Services																			
<b>Proposed 1<sup>st</sup> Ship Date:</b>	Oct 17, 2017		<b>Estimated Sample Availability:</b>	Date provided at sample request.																			
<b>Change Type:</b>																							
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Assembly Materials																		
<input checked="" type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>	Mechanical Specification																		
<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process																		
<input type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>	Wafer Bump Process																		
<input checked="" type="checkbox"/>	Wafer Fab Site	<input type="checkbox"/>	Wafer Fab Materials	<input type="checkbox"/>	Wafer Fab Process																		
		<input type="checkbox"/>	Part number change																				
<b>PCN Details</b>																							
<b>Description of Change:</b>																							
<b>The purpose of this Rev A PCN is to update the description of change section of this notification.</b>																							
This change notification is to announce the qualification of MIHO8 as an additional wafer fab site option for the LBC7 devices listed in the product affected section of this document.																							
<table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th colspan="3">Current Sites</th> <th colspan="3">Additional Sites</th> </tr> <tr> <th>Current Fab Site</th> <th>Fab Process</th> <th>Wafer Diameter</th> <th>Additional Fab Site</th> <th>Fab Process</th> <th>Wafer Diameter</th> </tr> </thead> <tbody> <tr> <td>FR-BIP-1</td> <td>LBC7</td> <td>200 mm</td> <td>MIHO8</td> <td>LBC7</td> <td>200 mm</td> </tr> </tbody> </table>						Current Sites			Additional Sites			Current Fab Site	Fab Process	Wafer Diameter	Additional Fab Site	Fab Process	Wafer Diameter	FR-BIP-1	LBC7	200 mm	MIHO8	LBC7	200 mm
Current Sites			Additional Sites																				
Current Fab Site	Fab Process	Wafer Diameter	Additional Fab Site	Fab Process	Wafer Diameter																		
FR-BIP-1	LBC7	200 mm	MIHO8	LBC7	200 mm																		
<b>In addition to the qualification of MIHO8, the die on the MLVD206 device will be replaced with the newer MLVD206B die to achieve better ESD and noise immunity. There is no change to the datasheet as a result of this change.</b>																							
The LBC7 process was previously qualified at MIHO on 1/14/2005. Qualification details are shown in the Qual Data Section of this document.																							
<b>Reason for Change:</b>																							
Continuity of Supply																							
<b>Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):</b>																							
None																							
<b>Changes to product identification resulting from this PCN:</b>																							
<b>Current:</b>																							
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<b>MIHO8</b>	<b>MH8</b>	<b>JPN</b>	<b>Ibaraki</b>																				
Sample product shipping label (not actual product label)																							

 <b>TEXAS INSTRUMENTS</b> MADE IN: Malaysia 2DC: 2Q:		 <b>G4</b>		(1P) SN74LS07NSR (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY (1T) 7523483SI2 (P) (2P) REV: (V) 0033317 (20L) CS0: SHP (21L) CCO: USA (22L) AS0: MLA (23L) AC0: MYS
MSL 2 / 260C / 1 YEAR MSL 1 / 235C / UNLIM	SEAL DT 03/29/04	OPT: ITEM: 39 <b>LBL: 5A (L)T0:1750</b>		
<b>Product Affected:</b>				
SN65MLVD206D	SN65MLVD206DR			

### Qualification Report

**SN65MLVD206**  
**Approve Date 14-June-2017**

#### Product Attributes

Attributes	Qual Device: SN65MLVD206	QBS Process Reference: TPS62110RSA	QBS Package Reference: LM358DR	QBS Package Reference: TL494IDR
Assembly Site	FMX	CAR	FMX	FMX
Package Family	SOIC	QFN	SOIC	SOIC
Wafer Fab Supplier	MIHO8	MIHO8	SFAB	SFAB
Wafer Fab Process	LBC7	LBC7	JI-SLM	JI-LIN

- QBS: Qual By Similarity
- Qual Device SN65MLVD206BD is qualified at LEVEL1-260C

## Qualification Results

**Data Displayed as: Number of lots / Total sample size / Total failed**

Type	Test Name / Condition	Duration	Qual Device: SN65MLVD206	QBS Process Reference: TPS62110RSA	QBS Package Reference: LM358DR	QBS Package Reference: TL494IDR
AC	Autoclave 121C	96 Hours	1/77/0	3/231/0	1/77/0	3/231/0
CDM	ESD - CDM	1500 V	1/3/0	-	-	-
ED	Electrical Characterization	Per Datasheet Parameters	Pass	-	-	-
ELFR	Early Life Failure Rate, 140C	48 Hours	-	3/1881/0	-	-
FLAM	Flammability (IEC 695-2-2)	--	-	-	-	3/15/0
FLAM	Flammability (UL 94V-0)	--	-	-	-	3/15/0
FLAM	Flammability (UL-1694)	--	-	-	-	3/15/0
HAST	Biased HAST, 130C/85%RH	96 Hours	-	3/231/0	1/77/0	3/229/0
HBM	ESD - HBM	4000 V	1/3/0	-	-	-
HBM	ESD - HBM (pins 6,7 only)	16000 V	1/3/0	-	-	-
HTOL	Life Test, 140C	480 Hours	-	3/231/0	-	-
HTOL	Life Test, 150C	300 Hours	-	-	1/77/0	3/231/0
HTSL	High Temp Storage Bake 170C	420 Hours	-	3/231/0	1/77/0	3/231/0
LU	Latch-up	( Per JESD78 )	1/6/0	-	-	-
TC	Temperature Cycle, -65/150C	500 Cycles	1/77/0	3/231/0	3/231/0	3/231/0
TS	Thermal Shock -65/150C	500 Cycles	-	3/231/0	3/231/0	3/231/0
WBP	Bond Pull	Wires	1/76/0	-	-	-
WBS	Ball Bond Shear	Wires	1/76/0	-	-	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

**Green/Pb-free Status:**

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	<a href="mailto:PCNAmericasContact@list.ti.com">PCNAmericasContact@list.ti.com</a>
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Asia Pacific	<a href="mailto:PCNAsiaContact@list.ti.com">PCNAsiaContact@list.ti.com</a>
Japan	<a href="mailto:PCNJapanContact@list.ti.com">PCNJapanContact@list.ti.com</a>